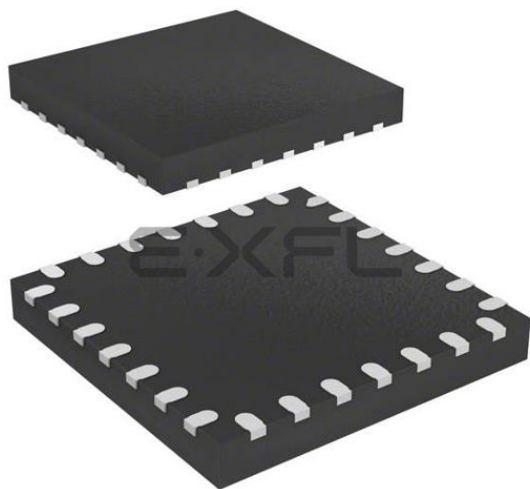




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, HDMI-CEC, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	24
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 13x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-UFQFN
Supplier Device Package	28-UFQFPN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f042g4u6tr

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sensor, voltage reference, VBAT voltage measurement) channels and performs conversions in single-shot or scan modes. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

3.10.1 Temperature sensor

The temperature sensor (TS) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Table 3. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at a temperature of 30 °C (± 5 °C), $V_{DDA} = 3.3$ V (± 10 mV)	0x1FFF F7B8 - 0x1FFF F7B9
TS_CAL2	TS ADC raw data acquired at a temperature of 110 °C (± 5 °C), $V_{DDA} = 3.3$ V (± 10 mV)	0x1FFF F7C2 - 0x1FFF F7C3

3.10.2 Internal voltage reference (V_{REFINT})

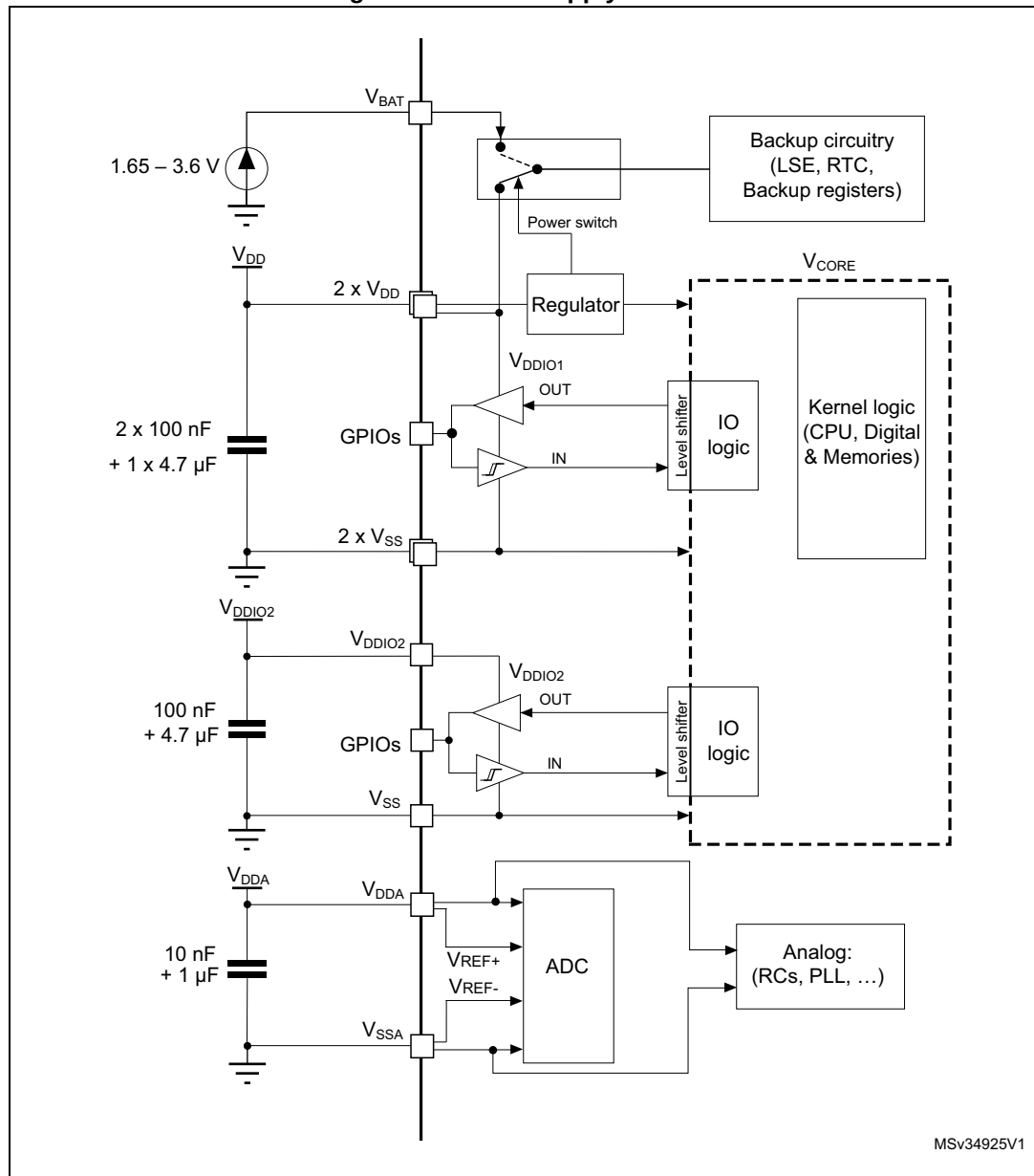
The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC. V_{REFINT} is internally connected to the ADC_IN17 input channel. The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 4. Internal voltage reference calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at a temperature of 30 °C (± 5 °C), $V_{DDA} = 3.3$ V (± 10 mV)	0x1FFF F7BA - 0x1FFF F7BB

6.1.6 Power supply scheme

Figure 13. Power supply scheme



Caution: Each power supply pair (V_{DD}/V_{SS} , V_{DDA}/V_{SSA} etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 18: Voltage characteristics](#), [Table 19: Current characteristics](#) and [Table 20: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 18. Voltage characteristics⁽¹⁾

Symbol	Ratings	Min	Max	Unit
$V_{DD}-V_{SS}$	External main supply voltage	- 0.3	4.0	V
$V_{DDIO2}-V_{SS}$	External I/O supply voltage	- 0.3	4.0	V
$V_{DDA}-V_{SS}$	External analog supply voltage	- 0.3	4.0	V
$V_{DD}-V_{DDA}$	Allowed voltage difference for $V_{DD} > V_{DDA}$	-	0.4	V
$V_{BAT}-V_{SS}$	External backup supply voltage	- 0.3	4.0	V
$V_{IN}^{(2)}$	Input voltage on FT and FTf pins	$V_{SS} - 0.3$	$V_{DDIOx} + 4.0^{(3)}$	V
	Input voltage on TTa pins	$V_{SS} - 0.3$	4.0	V
	Input voltage on any other pin	$V_{SS} - 0.3$	4.0	V
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	mV
$ V_{SSx} - V_{SS} $	Variations between all the different ground pins	-	50	mV
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see Section 6.3.12: Electrical sensitivity characteristics		-

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to [Table 19: Current characteristics](#) for the maximum allowed injected current values.
3. Valid only if the internal pull-up/pull-down resistors are disabled. If internal pull-up or pull-down resistor is enabled, the maximum limit is 4 V.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (for example control registers)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 46. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8/48 MHz	
S_{EMI}	Peak level	$V_{DD} = 3.6\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$, LQFP48 package compliant with IEC 61967-2	0.1 to 30 MHz	-9	dB μ V
			30 to 130 MHz	9	
			130 MHz to 1 GHz	17	
			EMI Level	3	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts $\times$ (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 47. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Packages	Class	Maximum value ⁽¹⁾	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	$T_A = +25\text{ }^{\circ}\text{C}$, conforming to JESD22-A114	All	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	$T_A = +25\text{ }^{\circ}\text{C}$, conforming to ANSI/ESD STM5.3.1	All	C4	500	V

1. Data based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 48. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DDIOx} (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the $-5\text{ }\mu\text{A}/+0\text{ }\mu\text{A}$ range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in [Table 49](#).

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

Figure 22. TC and TTa I/O input characteristics

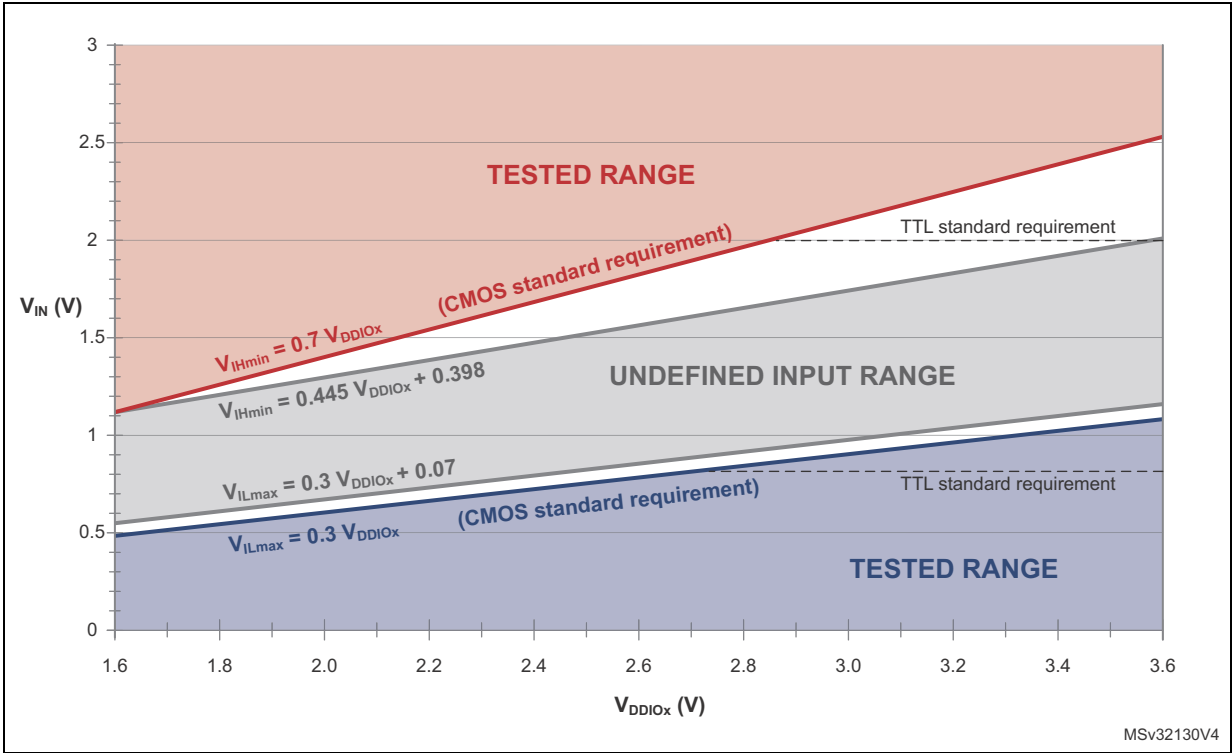
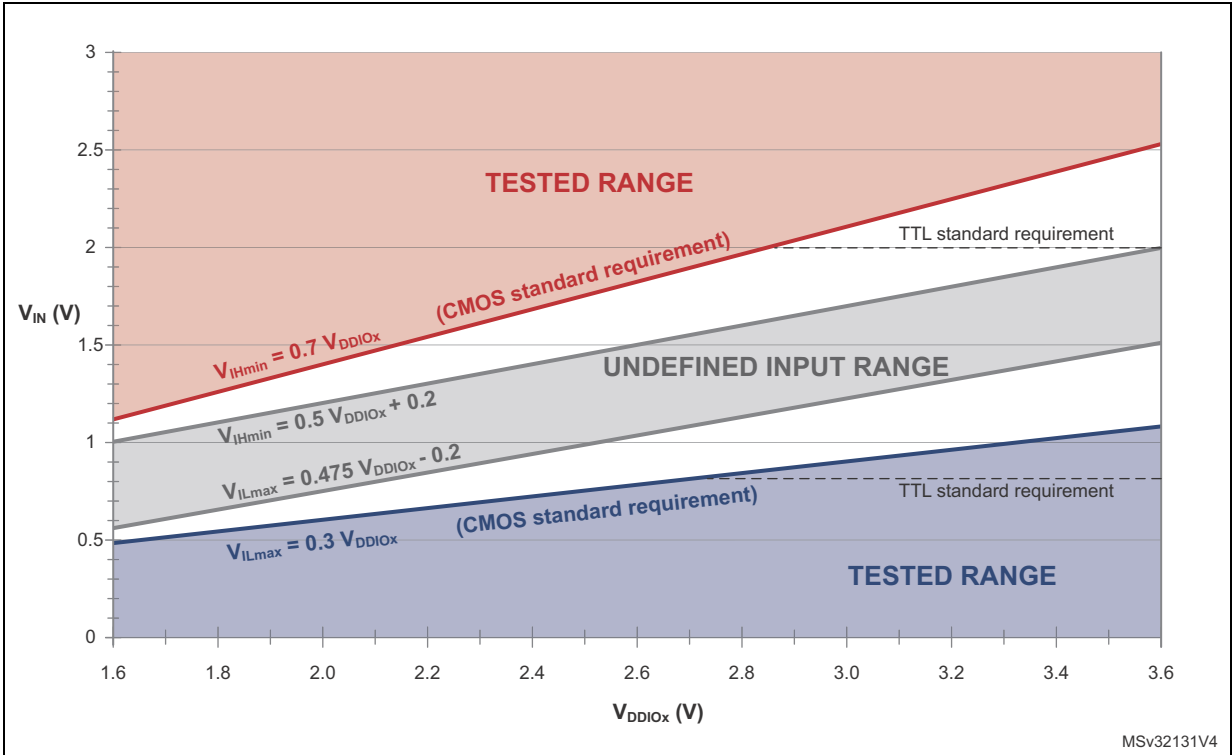


Figure 23. Five volt tolerant (FT and FTf) I/O input characteristics



Input/output AC characteristics

The definition and values of input/output AC characteristics are given in [Figure 24](#) and [Table 52](#), respectively. Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in [Table 21: General operating conditions](#).

Table 52. I/O AC characteristics⁽¹⁾⁽²⁾

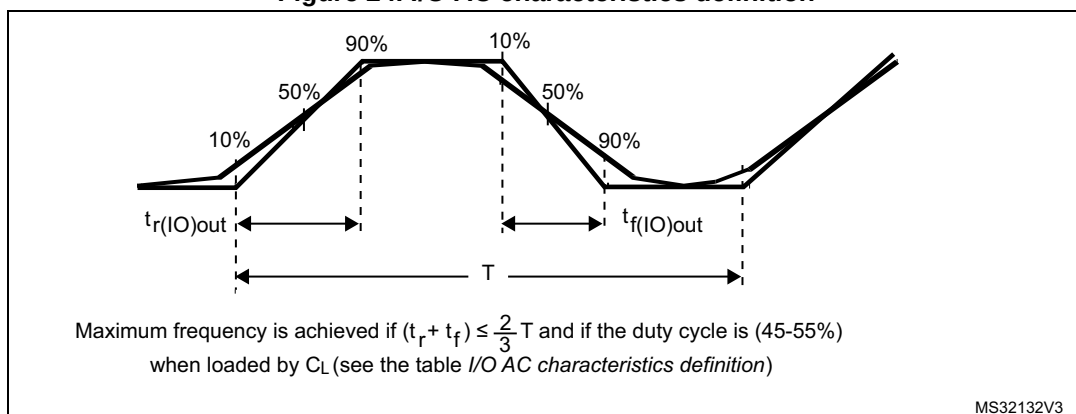
OSPEEDRy [1:0] value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max	Unit
x0	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}, V_{\text{DDIOx}} \geq 2 \text{ V}$	-	2	MHz
	$t_{\text{f}(\text{IO})\text{out}}$	Output fall time		-	125	ns
	$t_{\text{r}(\text{IO})\text{out}}$	Output rise time		-	125	
	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}, V_{\text{DDIOx}} < 2 \text{ V}$	-	1	MHz
	$t_{\text{f}(\text{IO})\text{out}}$	Output fall time		-	125	ns
	$t_{\text{r}(\text{IO})\text{out}}$	Output rise time		-	125	
01	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}, V_{\text{DDIOx}} \geq 2 \text{ V}$	-	10	MHz
	$t_{\text{f}(\text{IO})\text{out}}$	Output fall time		-	25	ns
	$t_{\text{r}(\text{IO})\text{out}}$	Output rise time		-	25	
	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}, V_{\text{DDIOx}} < 2 \text{ V}$	-	4	MHz
	$t_{\text{f}(\text{IO})\text{out}}$	Output fall time		-	62.5	ns
	$t_{\text{r}(\text{IO})\text{out}}$	Output rise time		-	62.5	
11	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 30 \text{ pF}, V_{\text{DDIOx}} \geq 2.7 \text{ V}$	-	50	MHz
			$C_L = 50 \text{ pF}, V_{\text{DDIOx}} \geq 2.7 \text{ V}$	-	30	
			$C_L = 50 \text{ pF}, 2 \text{ V} \leq V_{\text{DDIOx}} < 2.7 \text{ V}$	-	20	
			$C_L = 50 \text{ pF}, V_{\text{DDIOx}} < 2 \text{ V}$	-	10	
	$t_{\text{f}(\text{IO})\text{out}}$	Output fall time	$C_L = 30 \text{ pF}, V_{\text{DDIOx}} \geq 2.7 \text{ V}$	-	5	ns
			$C_L = 50 \text{ pF}, V_{\text{DDIOx}} \geq 2.7 \text{ V}$	-	8	
			$C_L = 50 \text{ pF}, 2 \text{ V} \leq V_{\text{DDIOx}} < 2.7 \text{ V}$	-	12	
			$C_L = 50 \text{ pF}, V_{\text{DDIOx}} < 2 \text{ V}$	-	25	
	$t_{\text{r}(\text{IO})\text{out}}$	Output rise time	$C_L = 30 \text{ pF}, V_{\text{DDIOx}} \geq 2.7 \text{ V}$	-	5	
			$C_L = 50 \text{ pF}, V_{\text{DDIOx}} \geq 2.7 \text{ V}$	-	8	
			$C_L = 50 \text{ pF}, 2 \text{ V} \leq V_{\text{DDIOx}} < 2.7 \text{ V}$	-	12	
			$C_L = 50 \text{ pF}, V_{\text{DDIOx}} < 2 \text{ V}$	-	25	

Table 52. I/O AC characteristics⁽¹⁾⁽²⁾ (continued)

OSPEEDRx[1:0] value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max	Unit
Fm+ configuration ⁽⁴⁾	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{\text{DDIOx}} \geq 2 \text{ V}$	-	2	MHz
	$t_{f(\text{IO})\text{out}}$	Output fall time		-	12	ns
	$t_{r(\text{IO})\text{out}}$	Output rise time		-	34	
	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{\text{DDIOx}} < 2 \text{ V}$	-	0.5	MHz
	$t_{f(\text{IO})\text{out}}$	Output fall time		-	16	ns
	$t_{r(\text{IO})\text{out}}$	Output rise time		-	44	
-	$t_{\text{EXTI}pw}$	Pulse width of external signals detected by the EXTI controller	-	10	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the STM32F0xxx RM0091 reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design, not tested in production.
3. The maximum frequency is defined in [Figure 24](#).
4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the STM32F0xxx reference manual RM0091 for a detailed description of Fm+ I/O configuration.

Figure 24. I/O AC characteristics definition



6.3.15 NRST pin characteristics

The NRST pin input driver uses the CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} .

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in [Table 21: General operating conditions](#).

Table 53. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(\text{NRST})}$	NRST input low level voltage	-	-	-	$0.3 V_{\text{DD}} + 0.07^{(1)}$	V
$V_{IH(\text{NRST})}$	NRST input high level voltage	-	$0.445 V_{\text{DD}} + 0.398^{(1)}$	-	-	

Table 60. IWDG min/max timeout period at 40 kHz (LSI)⁽¹⁾

Prescaler divider	PR[2:0] bits	Min timeout RL[11:0]= 0x000	Max timeout RL[11:0]= 0xFFFF	Unit
/4	0	0.1	409.6	ms
/8	1	0.2	819.2	
/16	2	0.4	1638.4	
/32	3	0.8	3276.8	
/64	4	1.6	6553.6	
/128	5	3.2	13107.2	
/256	6 or 7	6.4	26214.4	

1. These timings are given for a 40 kHz clock but the microcontroller internal RC frequency can vary from 30 to 60 kHz. Moreover, given an exact RC oscillator frequency, the exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there is always a full RC period of uncertainty.

Table 61. WWDG min/max timeout value at 48 MHz (PCLK)

Prescaler	WDGTB	Min timeout value	Max timeout value	Unit
1	0	0.0853	5.4613	ms
2	1	0.1706	10.9226	
4	2	0.3413	21.8453	
8	3	0.6826	43.6906	

6.3.20 Communication interfaces

I²C interface characteristics

The I²C interface meets the timings requirements of the I²C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I²C timings requirements are guaranteed by design when the I2Cx peripheral is properly configured (refer to Reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DDIOx} is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement. Refer to [Section 6.3.14: I/O port characteristics](#) for the I²C I/Os characteristics.

All I²C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:

Table 62. I²C analog filter characteristics⁽¹⁾

Symbol	Parameter	Min	Max	Unit
t_{AF}	Maximum width of spikes that are suppressed by the analog filter	50 ⁽²⁾	260 ⁽³⁾	ns

1. Guaranteed by design, not tested in production.
2. Spikes with widths below $t_{AF(min)}$ are filtered.
3. Spikes with widths above $t_{AF(max)}$ are not filtered

SPI/I²S characteristics

Unless otherwise specified, the parameters given in [Table 63](#) for SPI or in [Table 64](#) for I²S are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and supply voltage conditions summarized in [Table 21: General operating conditions](#).

Refer to [Section 6.3.14: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

Table 63. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	18	MHz
		Slave mode	-	18	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 15 pF	-	6	ns
$t_{su(NSS)}$	NSS setup time	Slave mode	4Tpclk	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode	2Tpclk + 10	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode, $f_{PCLK} = 36$ MHz, presc = 4	Tpclk/2 - 2	Tpclk/2 + 1	
$t_{su(MI)}$ $t_{su(SI)}$	Data input setup time	Master mode	4	-	
		Slave mode	5	-	
$t_{h(MI)}$ $t_{h(SI)}$	Data input hold time	Master mode	4	-	
		Slave mode	5	-	
$t_{a(SO)}^{(2)}$	Data output access time	Slave mode, $f_{PCLK} = 20$ MHz	0	3Tpclk	
$t_{dis(SO)}^{(3)}$	Data output disable time	Slave mode	0	18	
$t_{v(SO)}$	Data output valid time	Slave mode (after enable edge)	-	22.5	
$t_{v(MO)}$	Data output valid time	Master mode (after enable edge)	-	6	
$t_{h(SO)}$ $t_{h(MO)}$	Data output hold time	Slave mode (after enable edge)	11.5	-	
		Master mode (after enable edge)	2	-	
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	25	75	%

1. Data based on characterization results, not tested in production.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Figure 28. SPI timing diagram - slave mode and CPHA = 0

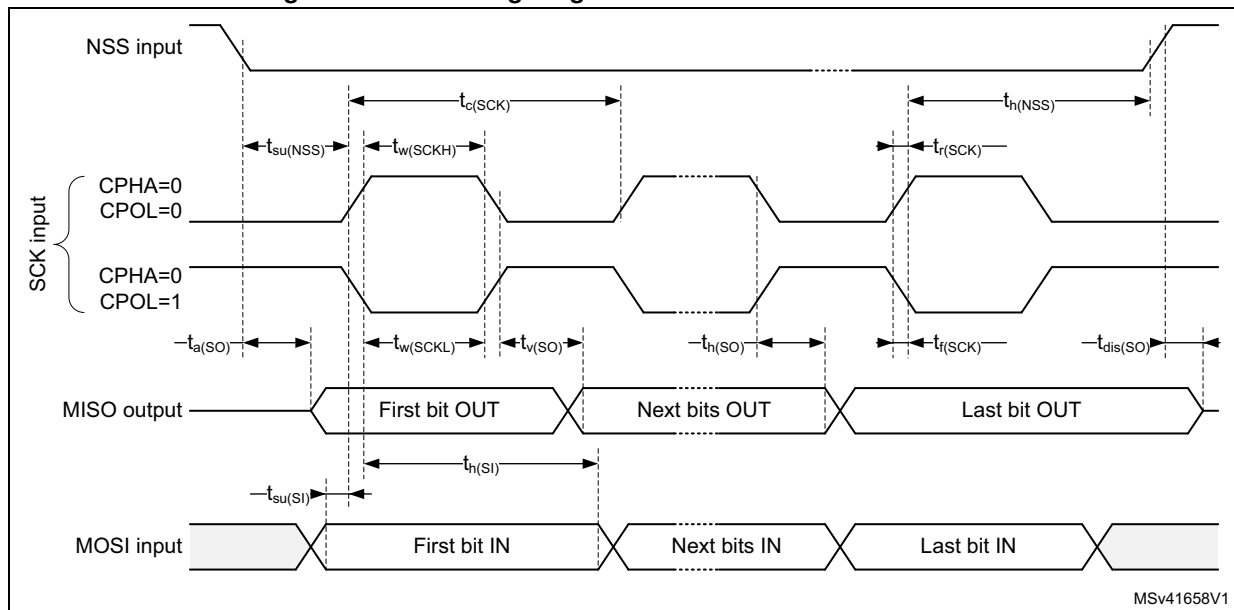
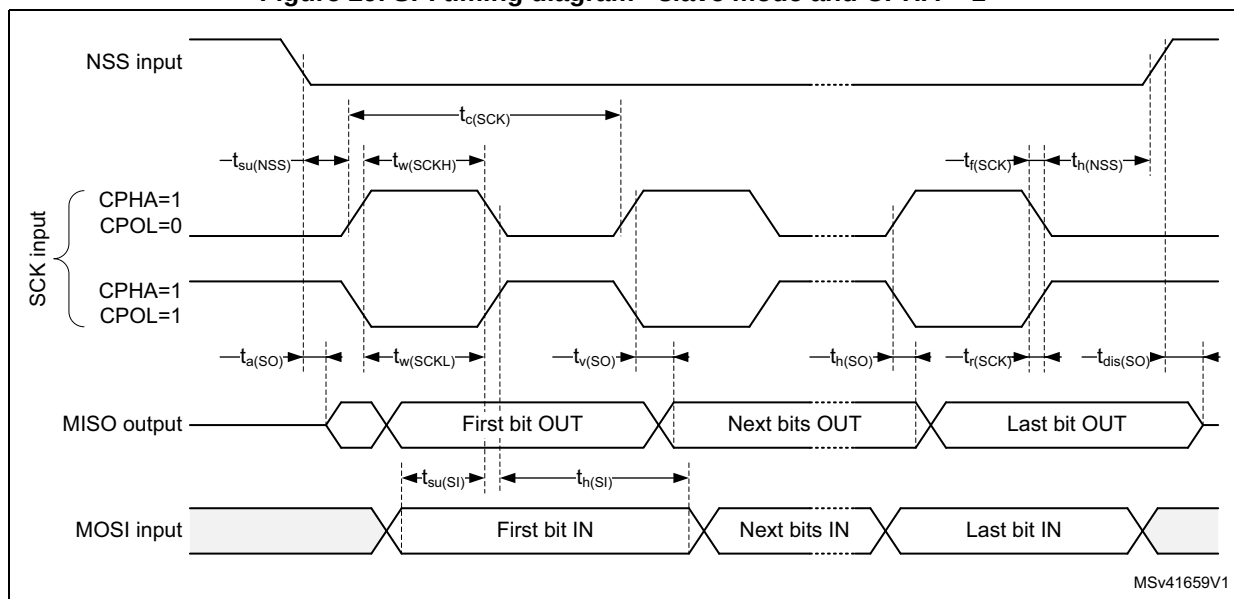


Figure 29. SPI timing diagram - slave mode and CPHA = 1

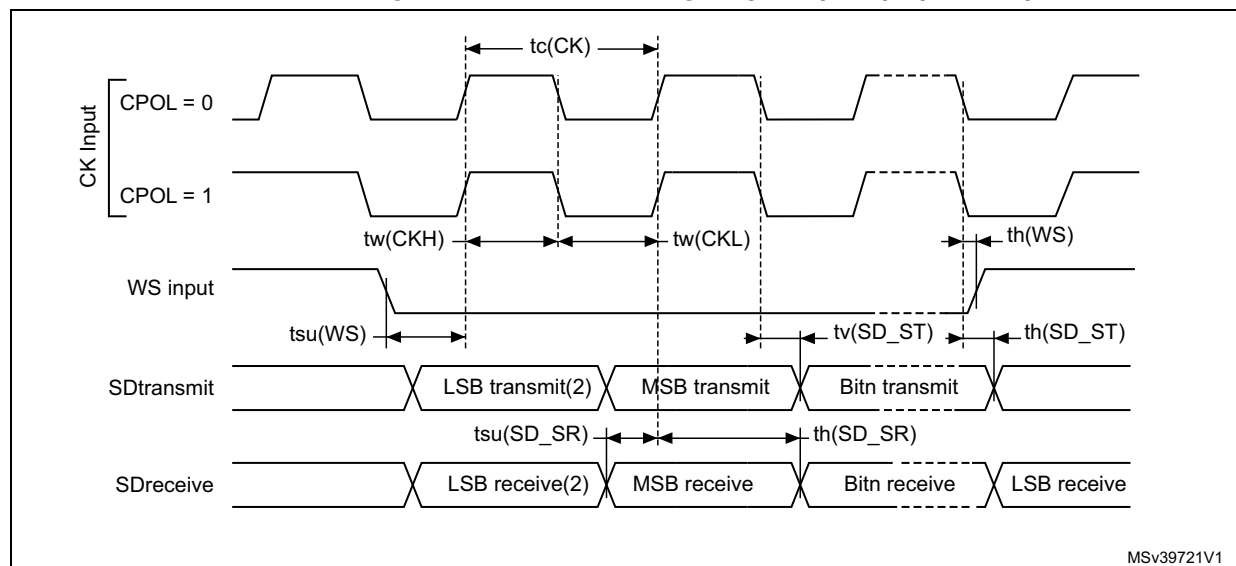


1. Measurement points are done at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD} .

Table 64. I²S characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{su}(SD_MR)$	Data input setup time	Master receiver	6	-	ns
$t_{su}(SD_SR)$		Slave receiver	2	-	
$t_h(SD_MR)^{(2)}$	Data input hold time	Master receiver	4	-	
$t_h(SD_SR)^{(2)}$		Slave receiver	0.5	-	
$t_v(SD_MT)^{(2)}$	Data output valid time	Master transmitter	-	4	
$t_v(SD_ST)^{(2)}$		Slave transmitter	-	20	
$t_h(SD_MT)$	Data output hold time	Master transmitter	0	-	
$t_h(SD_ST)$		Slave transmitter	13	-	

1. Data based on design simulation and/or characterization results, not tested in production.
2. Depends on f_{PCLK} . For example, if $f_{PCLK} = 8$ MHz, then $T_{PCLK} = 1/f_{PCLK} = 125$ ns.

Figure 31. I²S slave timing diagram (Philips protocol)

1. Measurement points are done at CMOS levels: $0.3 \times V_{DDIOx}$ and $0.7 \times V_{DDIOx}$.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

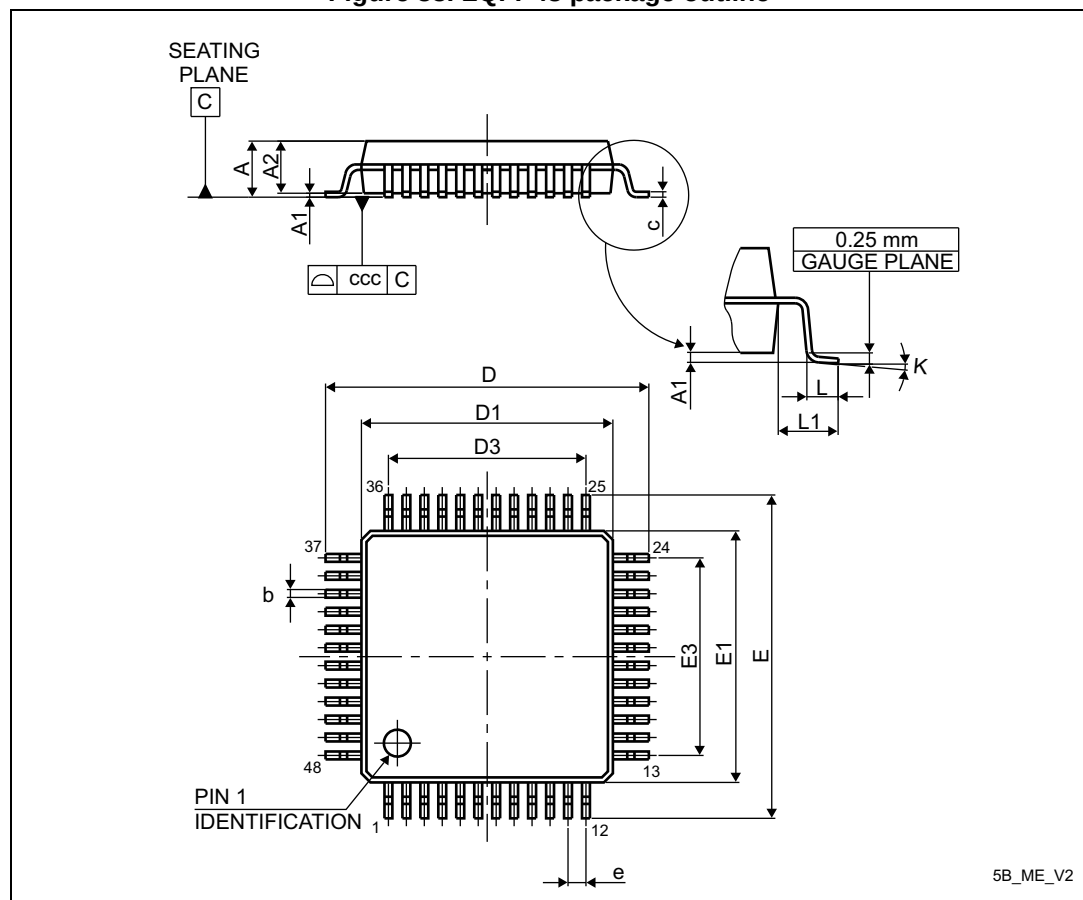
7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

7.1 LQFP48 package information

LQFP48 is a 48-pin, 7 x 7 mm low-profile quad flat package.

Figure 33. LQFP48 package outline

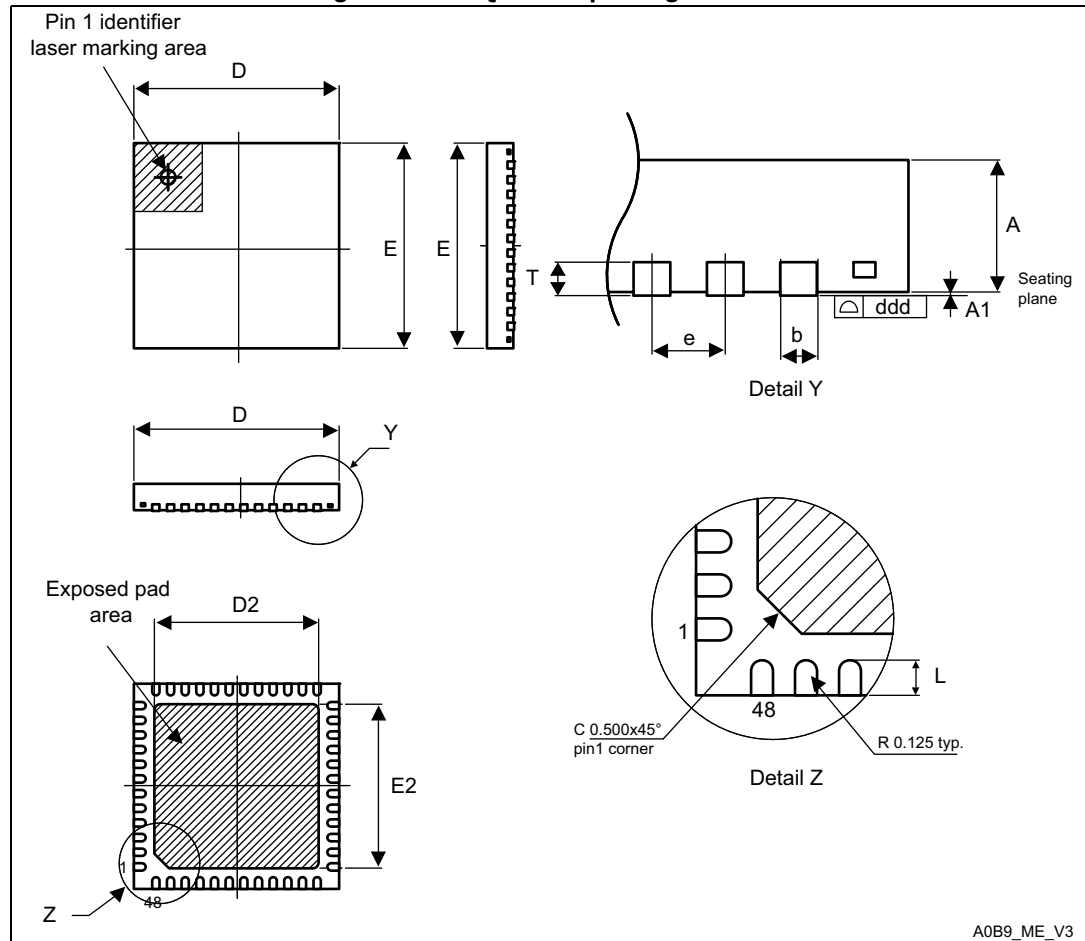


1. Drawing is not to scale.

7.2 UFQFPN48 package information

UFQFPN48 is a 48-lead, 7x7 mm, 0.5 mm pitch, ultra-thin fine-pitch quad flat package.

Figure 36. UFQFPN48 package outline

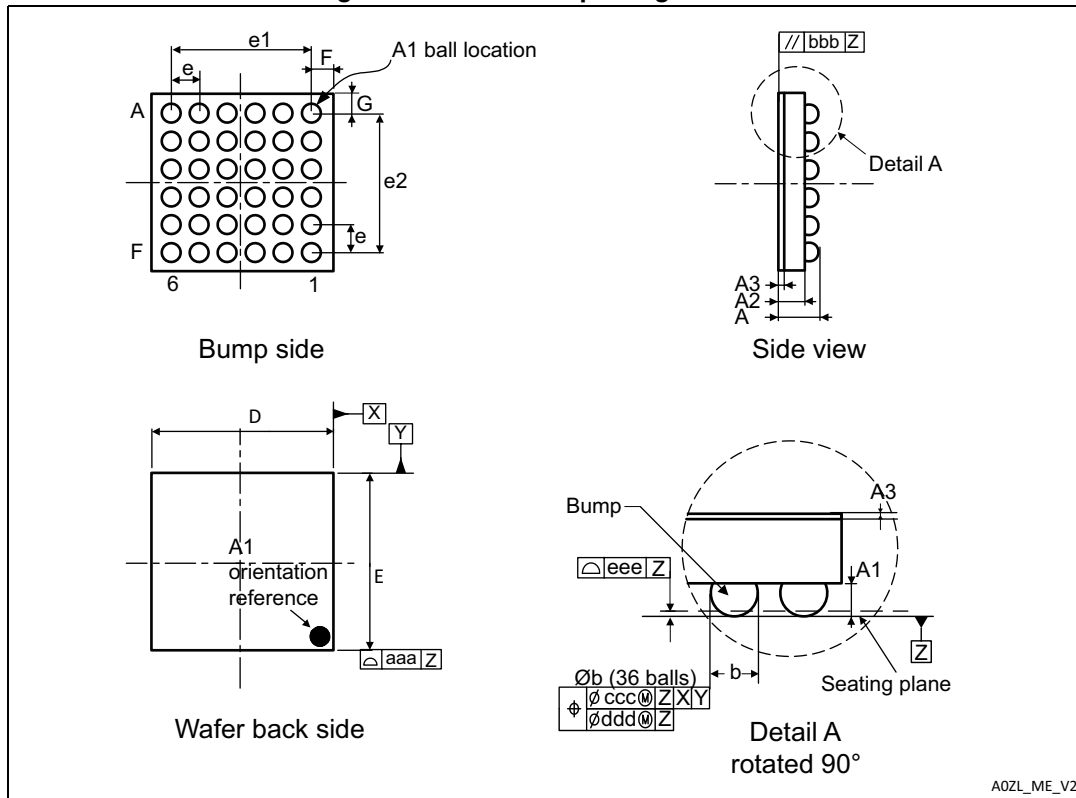


1. Drawing is not to scale.
2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

7.3 WLCSP36 package information

WLCSP36 is a 36-ball, 2.605 x 2.703 mm, 0.4 mm pitch wafer-level chip-scale package.

Figure 39. WLCSP36 package outline



1. Drawing is not to scale.

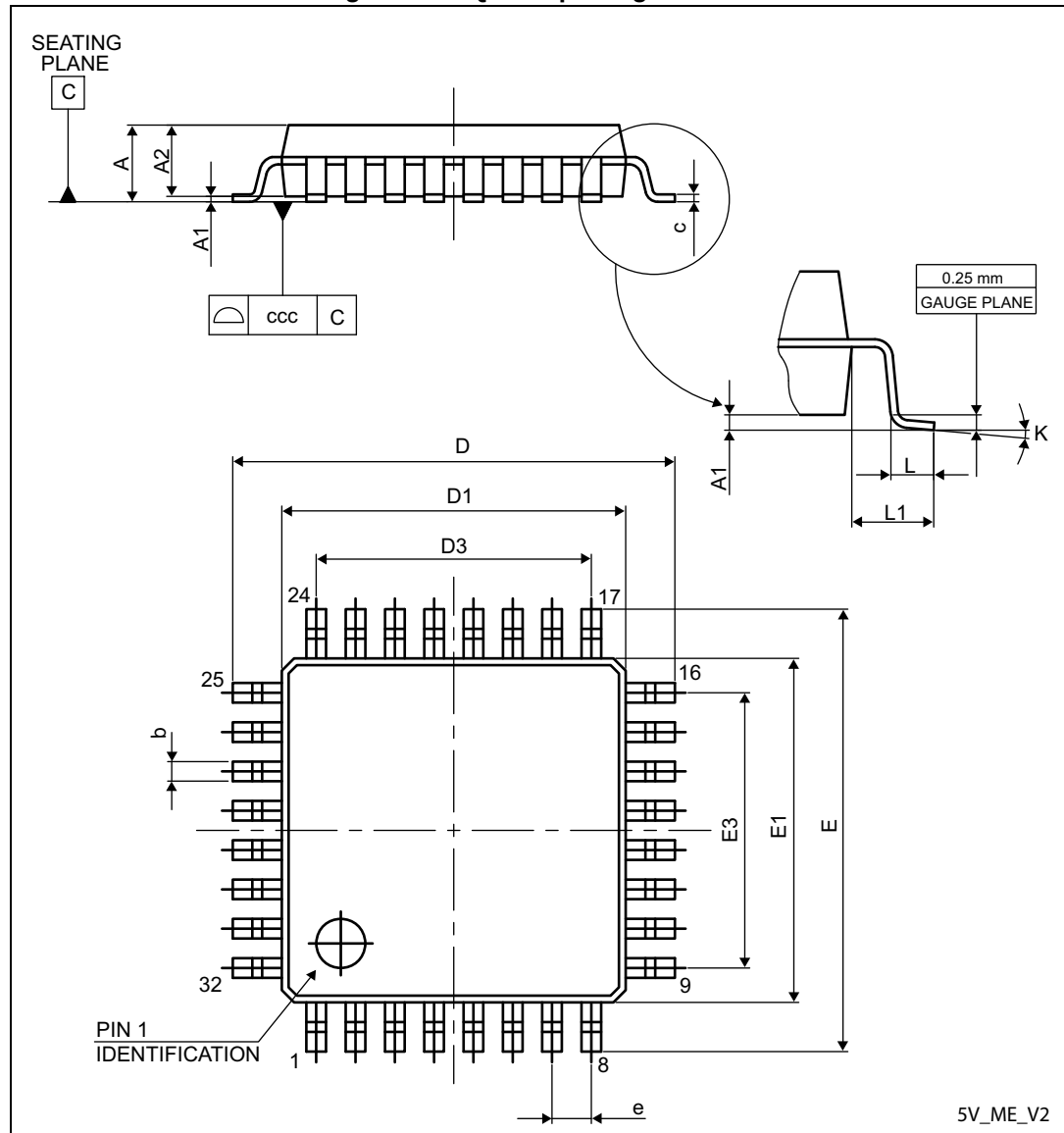
Table 68. WLCSP36 package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3 ⁽²⁾	-	0.025	-	-	0.0010	-
b ⁽³⁾	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	2.570	2.605	2.640	0.1012	0.1026	0.1039
E	2.668	2.703	2.738	0.1050	0.1064	0.1078
e	-	0.400	-	-	0.0157	-
e1	-	2.000	-	-	0.0787	-
e2	-	2.000	-	-	0.0787	-

7.4 LQFP32 package information

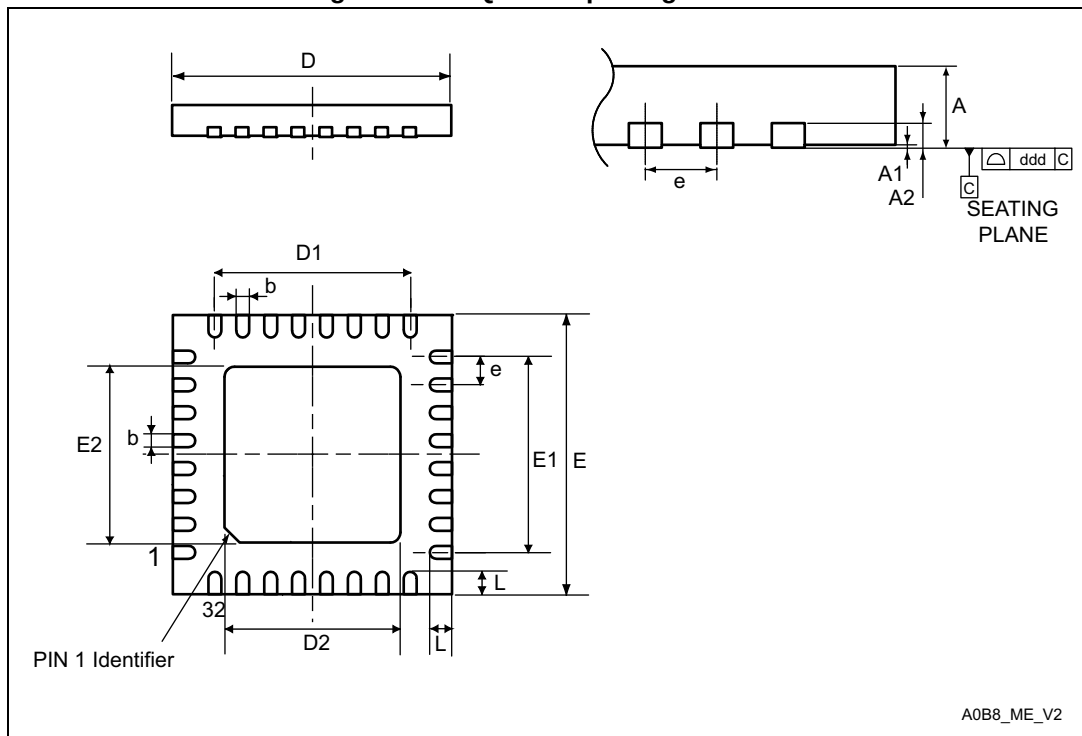
LQFP32 is a 32-pin, 7 x 7 mm low-profile quad flat package.

Figure 42. LQFP32 package outline



1. Drawing is not to scale.

Figure 45. UFQFPN32 package outline

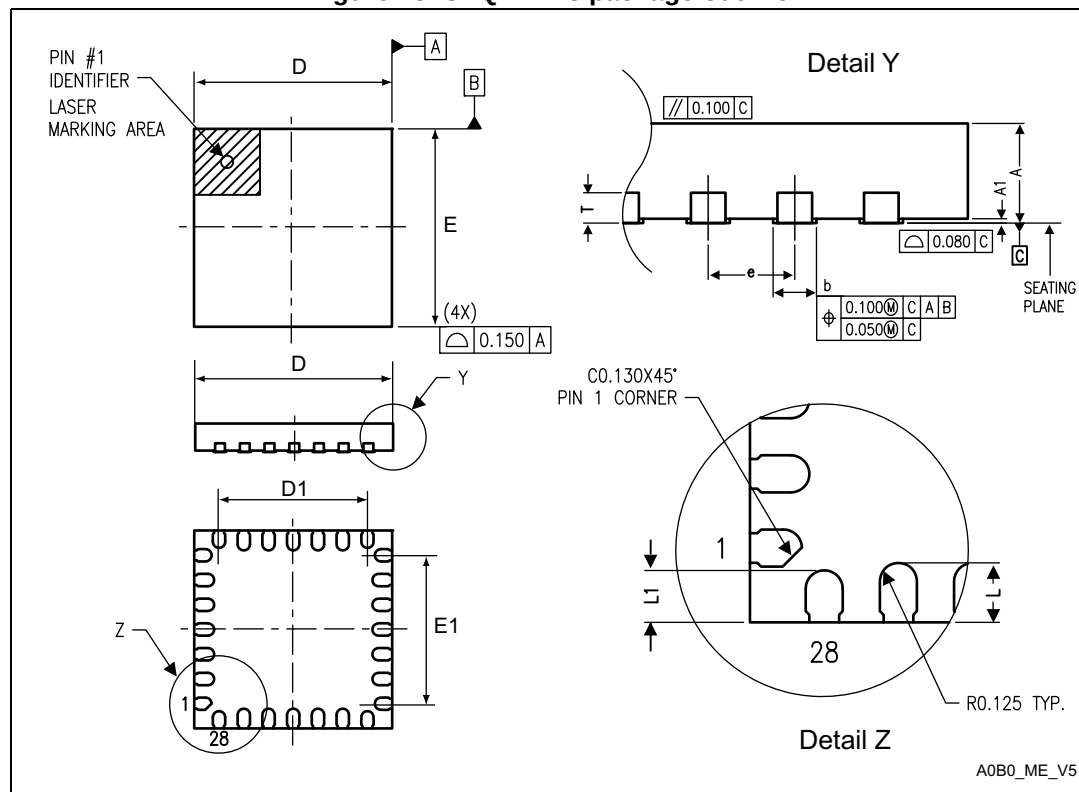


1. Drawing is not to scale.
2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
3. There is an exposed die pad on the underside of the UFQFPN package. This pad is used for the device ground and must be connected. It is referred to as pin 0 in *Table: Pin definitions*.

7.6 UFQFPN28 package information

UFQFPN28 is a 28-lead, 4x4 mm, 0.5 mm pitch, ultra-thin fine-pitch quad flat package.

Figure 48. UFQFPN28 package outline



1. Drawing is not to scale.

Table 72. UFQFPN28 package mechanical data⁽¹⁾

Symbol	millimeters			inches		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	-	0.000	0.050	-	0.0000	0.0020
D	3.900	4.000	4.100	0.1535	0.1575	0.1614
D1	2.900	3.000	3.100	0.1142	0.1181	0.1220
E	3.900	4.000	4.100	0.1535	0.1575	0.1614
E1	2.900	3.000	3.100	0.1142	0.1181	0.1220
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
L1	0.250	0.350	0.450	0.0098	0.0138	0.0177
T	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
e	-	0.500	-	-	0.0197	-

- Figure 49. Recommended footprint for UFQFPN28 package**

